TOSHIBA Intelligent Power Device Silicon Monolithic Power MOS Integrated Circuit

TPD2007F

Low-Side Power Switch Array (8 Channels) for Motors, Solenoids, and Lamp Drivers

The TPD2007F is an 8-channel low-side switch array. The IC has a vertical MOSFET output which can be directly driven from a CMOS or TTL logic circuit (e.g., an MPU). It offers overcurrent and overtemperature protection functions.

Features

- 8-channel low-side switch array incorporating an N-channel • power MOSFET (1.4 Ω max)
- Can directly drive a power load from a microprocessor. •
- Built-in protection against overtemperature and overcurrent •
- 8-channel access enables space-saving design.
- High operating voltage: 40 V
- Low on-resistance: $1.4 \Omega \max @V_{IN} = 5 V$, $I_D = 0.5 A$ (per channel) ٠
- Supports parallel operation. •
- Built-in active clamp circuit •
- Supplied in an SSOP-24 package (300 mil) in embossed taping.

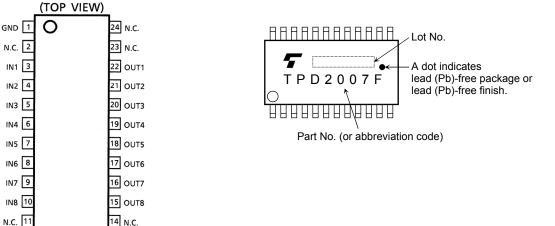
13 N.C.

Pin Assignment

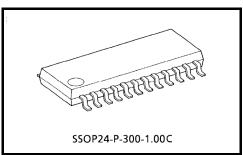
N.C. 11

GND

Marking



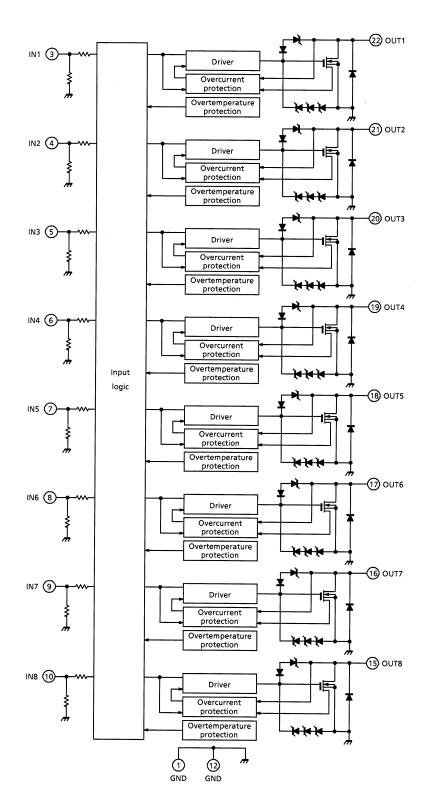
Note: This product has a MOS structure and is sensitive to electrostatic discharge. When handling this product, ensure that the environment is protected against electrostatic discharge.



Weight: 0.29 g (typ.)

TOSHIBA

Block Diagram

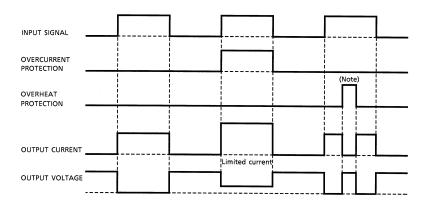


<u>TOSHIBA</u>

Pin Description

| Pin No. | Symbol | Description |
|---------|--------|---|
| 1 | GND | GND pin; in common with the pin no.12 internally. |
| 2 | N.C. | |
| 3 | IN1 | Control input pin for channel 1 and built-in pull-down resistor (300 k Ω typ.) |
| 4 | IN2 | Control input pin for channel 2 and built-in pull-down resistor (300 k Ω typ.) |
| 5 | IN3 | Control input pin for channel 3 and built-in pull-down resistor (300 k Ω typ.) |
| 6 | IN4 | Control input pin for channel 4 and built-in pull-down resistor (300 k Ω typ.) |
| 7 | IN5 | Control input pin for channel 5 and built-in pull-down resistor (300 k Ω typ.) |
| 8 | IN6 | Control input pin for channel 6 and built-in pull-down resistor (300 k Ω typ.) |
| 9 | IN7 | Control input pin for channel 7 and built-in pull-down resistor (300 k Ω typ.) |
| 10 | IN8 | Control input pin for channel 8 and built-in pull-down resistor (300 k Ω typ.) |
| 11 | N.C. | — |
| 12 | GND | GND pin; in common with the pin no.1 internally. |
| 13 | N.C. | _ |
| 14 | N.C. | — |
| 15 | OUT8 | Output pin for channel 8 |
| 16 | OUT7 | Output pin for channel 7 |
| 17 | OUT6 | Output pin for channel 6 |
| 18 | OUT5 | Output pin for channel 5 |
| 19 | OUT4 | Output pin for channel 4 |
| 20 | OUT3 | Output pin for channel 3 |
| 21 | OUT2 | Output pin for channel 2 |
| 22 | OUT1 | Output pin for channel 1 |
| 23 | N.C. | _ |
| 24 | N.C. | — |

Timing Chart



Note: The overheating detector circuits feature hysteresis. After overheating is detected, normal operation is restored only when the junction temperature falls by the hysteresis amount (10°C typ.) in relation to the overheating detection temperature.

Truth Table

| Input Signal | Output Signal | State | | |
|--------------|--------------------|----------------------------|--|--|
| L | Н | Normal | | |
| Н | L | Normai | | |
| L | Н | Overcurrent protection | | |
| Н | Internally limited | | | |
| L | Н | Overtemperature protection | | |
| Н | Н | Overtemperature protection | | |

Absolute Maximum Ratings (Ta = 25°C)

| Characteristic | Symbol | Rating | Unit | |
|-------------------------------------|------------------|-----------------------|------|--|
| Drain-source voltage | V _{DSS} | 40 | V | |
| Input voltage | V _{IN} | -0.5 ~ 7 | V | |
| Output current | ID | Internally Limited | А | |
| Power dissipation | Рт | 0.8 | W | |
| (operating all channels, ta = 25°C) | Γļ | 1.2 (Note) | | |
| Single pulse avalanche energy | E _{AS} | 10 | mJ | |
| Operating temperature | T _{opr} | -40 ~ 85 | °C | |
| Junction temperature | Тј | 150 | °C | |
| Storage temperature | T _{stg} | − 55 ~ 150 | °C | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

| Characteristic | Symbol | Rating | Unit | |
|--|------------------------|--------------|--------|--|
| Thermal resistance junction to | SD | 156.3 | °C / W | |
| ambient (operating all channels, ta = 25°c) | ΣR _{th (j-a)} | 104.2 (Note) | | |

Note: 60 mm × 60 mm × 1.6 mm when mounted on a glass epoxy PCB (DC)

Electrical Characteristics (Unless otherwise specified, T_i = 25°C)

| Characteristic | | Symbol | Test Circuit | Test Condition | Min | Тур. | Max | Unit | |
|---|-------------|---------------------|-----------------|--|-----|------|-----|------|--|
| Drain-source clamp voltage | | V (BR) DSS | _ | I _D = 10 mA, V _{IN} = 0 V | 40 | _ | _ | V | |
| Input voltage | | V _{th} | _ | V _{DS} = 24 V, I _{DS} = 1 mA | 0.8 | _ | 2.0 | V | |
| Input current | | IIL | _ | V _{IN} = 0 V | -10 | _ | 10 | μА | |
| | | Ι _{ΙΗ} | _ | V _{IN} = 5 V | - | 140 | 300 | μA | |
| On resistance | | R _{DS(ON)} | _ | V _{IN} = 5 V, I _{O =} 0.5 A | - | 1.0 | 1.4 | Ω | |
| Off current | | I _{DSS} | _ | V _{DS} = 40V | - | — | 100 | μA | |
| Overcurrent protection | | I _{S(1)} | - | V_{DS} = 12 V, V_{IN} = 5 V, R _L = 3 Ω | 1 | 2 | 3 | A | |
| | | I _{S(2)} | _ | V_{DS} = 30 V, V_{IN} = 5 V, R _L = 3Ω | 0.7 | _ | 2 | | |
| Overtemperature | Temperature | TSD | _ | V _{IN} = 5 V | _ | 160 | _ | °C | |
| Protection | Hysteresis | ΔTSD | _ | — | _ | 10 | _ | | |
| Switching time | | t _{ON} | 1 | V _{DD} = 12 V, R _L = 24Ω, V _{IN} = 0 V / 5 V | _ | 10 | 50 | μs | |
| | | tOFF | 1 | | _ | 10 | 50 | | |
| Operating input voltage protection circuit | | V _{IN(P)} | _ | _ | 3.9 | _ | 6.0 | V | |
| Drain-source diode forward voltage | | V _{DSF} | _ | IF = 1 A, V _{IN} = 0 V | _ | _ | 1.6 | V | |

Description of Protector Circuit

(1) **Overtemperature Protection**

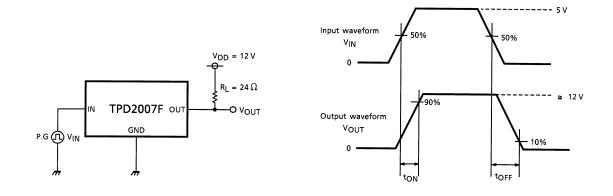
• The overheating detector circuits feature hysteresis. After overheating is detected, normal operation is restored only when the junction temperature falls by the hysteresis amount (10°C typ.) in relation to the overheating detection temperature.

(2) Overcurrent Protection

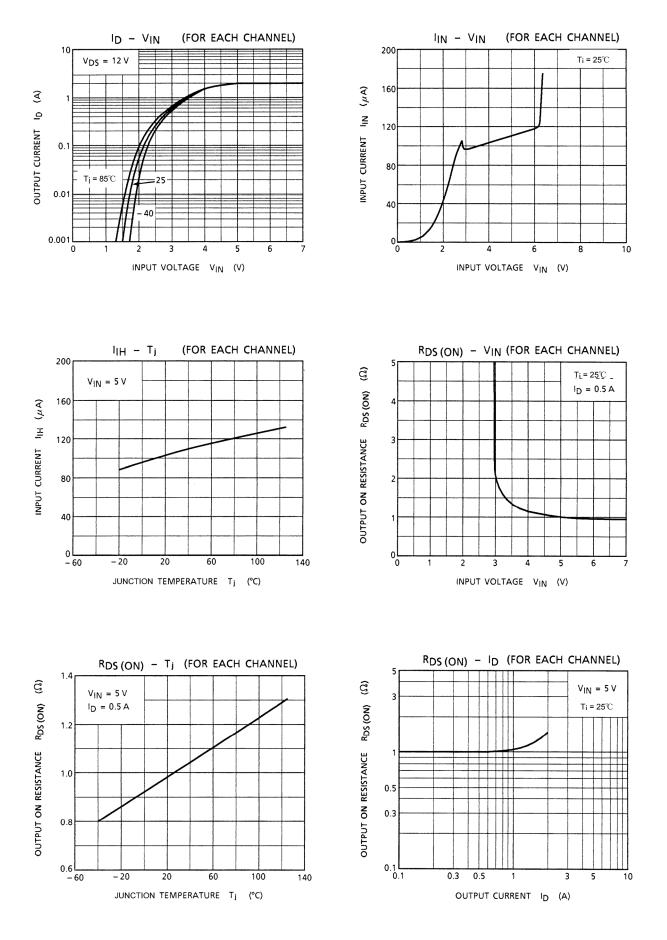
• When overcurrent is detected, the overcurrent limiter function limits the output current. Normal operation is restored when the load current drops below the overcurrent detection value.

Test Circuit

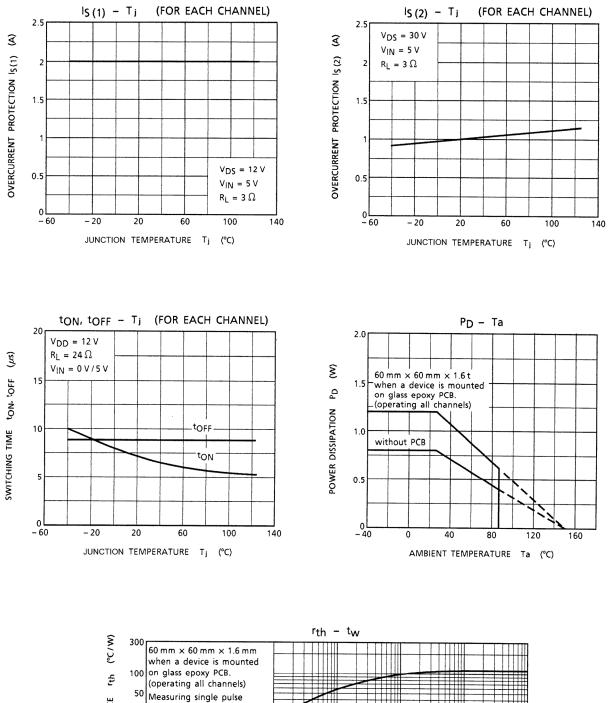
Switching Time

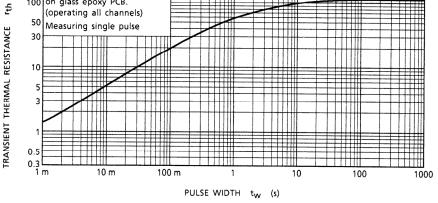


TOSHIBA



TOSHIBA





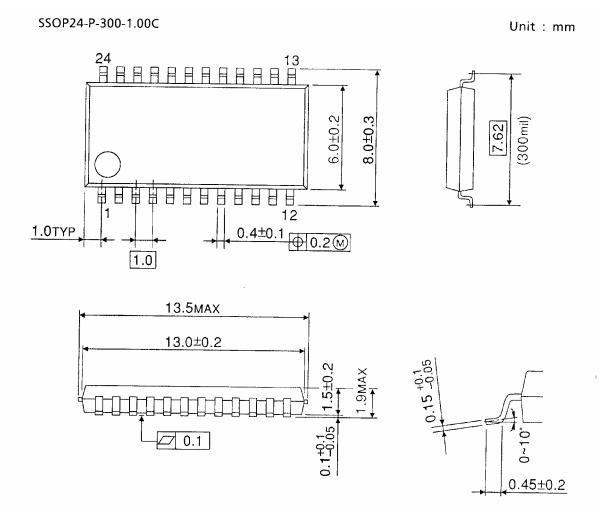
Moisture-Proof Packing

After the pack is opened, the devices should be used within 48 hours and in a 30°C, 60% RH environment. Embossed-tape packing cannot be baked. Devices so packed must be within their allowable time limits after unpacking, as specified on the packing.

Standard tape packing quantity: 2000 devices / reel (EL1)

<u>TOSHIBA</u>

Package Dimensions



Weight: 0.29 g (typ.)

RESTRICTIONS ON PRODUCT USE

20070701-EN

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.).These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patents or other rights of TOSHIBA or the third parties.
- Please contact your sales representative for product-by-product details in this document regarding RoHS compatibility. Please use these products in this document in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses occurring as a result of noncompliance with applicable laws and regulations.